

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

#29H Suppi Auot

Hiroyuki ABE et al.

Group Art Unit: 2814

M. Baunson

Application No.: 08/930,449

Examiner:

S. Rao

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125/03

Filed: October 7, 1997

Docket No.:

039514

For:

HIGH ENERGY SUPPLY APPARATUS, METHOD OF FORMING CRYSTALLINE

FILM AND METHOD OF MANUFACTURING THIN FILM ELECTRONIC DEVICE

SUPPLEMENTAL AMENDMENT

Director of the U.S. Patent and Trademark Office Washington, D.C. 20231

Sir:

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As a supplement to the Amendment filed on December 12, 2002, and in response to the January 9 and 14, 2003 telephone interviews, please further amend the above-identified application as follows:

IN THE CLAIMS:

Please replace claims 1, 12, 20, 25, 30, 35, 40, 46 and 56 as follows:

1. (Seven Times Amended) A method of forming a crystalline film, comprising: forming a thin film having a surface on a glass substrate; and crystallizing at least a surface layer of the thin film by applying energy through a window that exhibits transparency to the energy to the surface of the thin film, wherein a distance between the window and the thin film is more than about 20 mm, and at least the surface layer of the thin film is melted by the applied energy and crystallized by cooling solidification under a hydrogen-containing atmosphere of at least atmospheric pressure,

wherein unpaired bonding electrons on the surface of the thin film during the cooling solidification are terminated by hydrogen atoms in the hydrogen-containing atmosphere of at least atmospheric pressure.

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